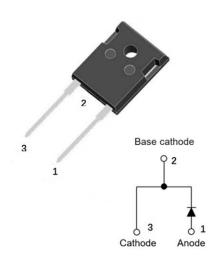
Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	55A
Q _C	209nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AC
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NGHD
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C			116
Continuous forward current @ T _C =135°C	I _F	А	55
Continuous forward current @ T _C =160°C			30
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	288
Power Dissipation@ T _C =25°C	0	10/	535
Power Dissipation@ T _C =110°C	P _{TOT}	W	232
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	414
Operating junction and Storage temperature range	$T_{j}\;,T_{stg}$	°C	-55 to +175

YJD112030NGHDQ

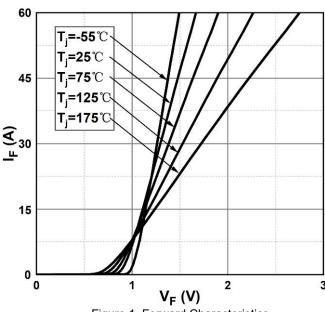
■Electrical Characteristics

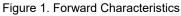
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drep		V	I _F =30A, T _j =25°C	1.29	1.55
Forward voltage drop	V _F	V	I _F =30A, T _j =175°C	1.71	-
Deverse leakage current	_		V _R =1200V, T _j =25°C	1	20
Reverse leakage current	I _R	μΑ	V _R =1200V, T _j =175°C	6	-
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C , Q_C = $\int_0^{VR} C(V) dV$	209	-
			V _R =0V, f=1MHZ	3078	-
Total capacitance	С	pF	V _R =400V, f=1MHZ	197	-
			V _R =800V, f=1MHZ	142	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	54	-

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\scriptscriptstyle{\theta J-C}}$	°C W	0.28

■Typical Characteristic





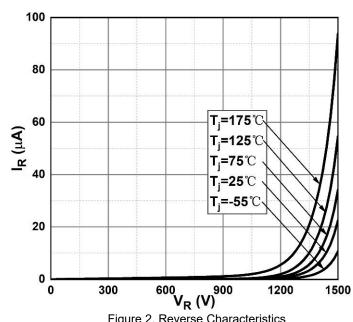
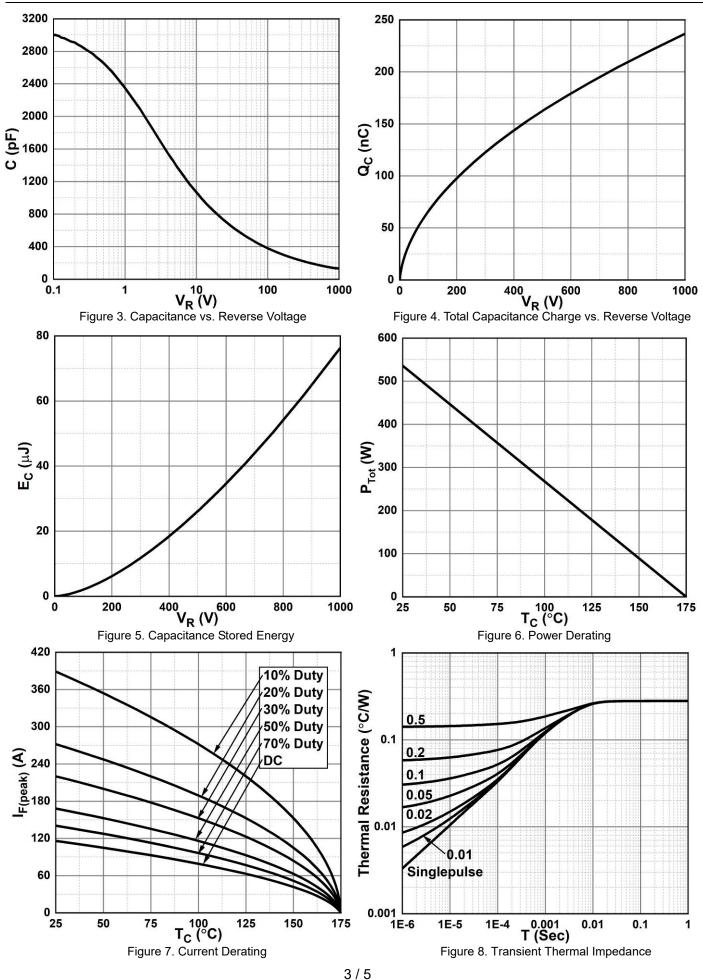


Figure 2. Reverse Characteristics

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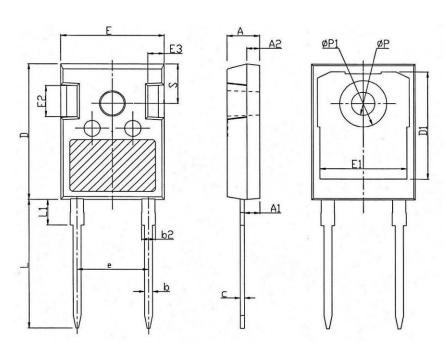






■Outline Dimensions





	TO-247AC					
Dim	Min	Max				
Α	4.80	5.20				
A1	2.21	2.61				
A2	1.85	2.15				
b	1.11	1.36				
b2	1.91	2.21				
С	0.51	0.75				
D	20.70	21.30				
D1	16.25	16.85				
Е	15.50	16.10				
E1	13.00	13.60				
E2	4.80	5.20				
E3	2.30	2.70				
е	10.88BSC					
L	19.62	20.22				
L1	-	4.30				
ΦР	3.40	3.80				
ФР1	-	7.30				
S	6.15BSC					



YJD112030NGHDQ



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